

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Previously Presented). A process for preparing a lithographic mask, comprising:

making patterns on a plane mask, the plane mask having an SOI structure, comprising a layer of semiconductor material, a buried layer of insulant and a substrate; and transferring the patterns and the plane mask to a curved support that includes at least one point of non-nil curvature.

Claim 2 (Previously Presented). The process according to claim 1, wherein the making includes utilizing electron beam lithography to make the patterns.

Claim 3 (Previously Presented). The process according to claim 1 or 2, further comprising thinning the substrate of the SOI structure.

Claim 4 (Previously Presented). The process according to claim 1 or 2, further comprising:

thinning the plane mask and installing a handle substrate before implementing the transferring.

Claim 5 (Previously Presented). The process according to claim 1 or 2, wherein the curved support includes metal, or glass or plastic material.

Claim 6 (Previously Presented). The process according to claim 1 or 2, further comprising:

deforming the curved support with the non-nil curvature while transferring the patterns and the plane mask to the curved support.

Claim 7 (Previously Presented). The process according to claim 1 or 2, wherein the making includes making the patterns with a dimension of between 50 nm and 10 μm .

Claims 8-10 (Canceled).

Claim 11 (Previously Presented). The process according to claim 1, wherein the transferring comprises:

affixing the plane mask to the curved support such that a surface of the plane mask that includes the patterns faces away from the curved support.

Claim 12 (Previously Presented). The process according to claim 1, further comprising:

disposing the curved support, with the patterns transferred thereto, to contact another substrate; and

causing the curved support, with the patterns transferred thereto, to rotate and transfer an image to the another substrate.

Claim 13 (New). The process according to claim 1, further comprising:

deforming, with an actuator, the curved support with the non-nil curvature while transferring the patterns and the plane mask to the curved support.

Claim 14 (New). The process according to claim 13, wherein the actuator is disposed within the curved surface.

Claim 15 (New). The process according to claim 1, wherein the making patterns includes forming the patterns only in a surface layer of the SOI structure.

Claim 16 (New). The process according to claim 15, further comprising:
separating the surface layer of the SOI structure from the substrate prior to the transferring.